

BUJD105AD

NPN power transistor with integrated diode

Rev. 02 — 29 July 2010

Product data sheet

1. Product profile

1.1 General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated anti-parallel E-C diode in a SOT428 (DPAK) surface-mountable plastic package.

1.2 Features and benefits

- Fast switching
- High voltage capability
- Very low switching and conduction losses

1.3 Applications

- DC-to-DC converters
- Electronic lighting ballasts
- Inverters
- Motor control systems

1.4 Quick reference data

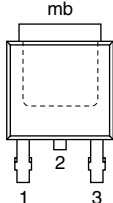
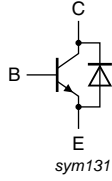
Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------|---|-----|------|-----|------|
| I_C | collector current | see Figure 1 ; see Figure 2 ; DC | - | - | 8 | A |
| P_{tot} | total power dissipation | $T_{mb} \leq 25\text{ °C}$; see Figure 3 | - | - | 80 | W |
| V_{CESM} | collector-emitter peak voltage | $V_{BE} = 0\text{ V}$ | - | - | 700 | V |
| Static characteristics | | | | | | |
| h_{FE} | DC current gain | $V_{CE} = 5\text{ V}$; $I_C = 4\text{ A}$; $T_{mb} = 25\text{ °C}$; see Figure 9 ; see Figure 10 | 8 | 12.5 | - | |



2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|--------------------------|---|---|
| 1 | B | base |  |  |
| 2 | C | collector ^[1] | | |
| 3 | E | emitter | | |

SOT428 (DPAK)

[1] It is not possible to make a connection to pin 2 of the SOT428 (DPAK) package.

3. Ordering information

Table 3. Ordering information

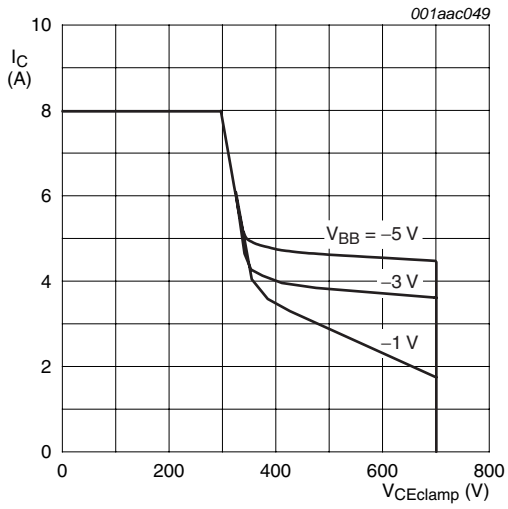
| Type number | Package | | Version |
|-------------|---------|---|---------|
| | Name | Description | |
| BUJD105AD | DPAK | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428 |

4. Limiting values

Table 4. Limiting values

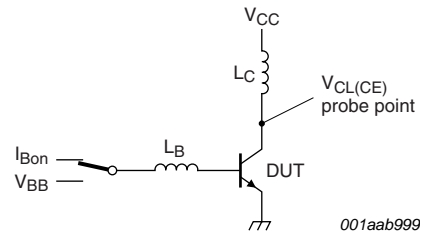
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------|--------------------------------|---|-----|-----|------|
| V_{CESM} | collector-emitter peak voltage | $V_{BE} = 0\text{ V}$ | - | 700 | V |
| V_{CBO} | collector-base voltage | $I_E = 0\text{ A}$ | - | 700 | V |
| V_{CEO} | collector-emitter voltage | $I_B = 0\text{ A}$ | - | 400 | V |
| I_C | collector current | DC; see Figure 1 ; see Figure 2 | - | 8 | A |
| I_{CM} | peak collector current | see Figure 1 ; see Figure 2 | - | 16 | A |
| I_B | base current | DC | - | 4 | A |
| I_{BM} | peak base current | | - | 8 | A |
| P_{tot} | total power dissipation | $T_{mb} \leq 25\text{ °C}$; see Figure 3 | - | 80 | W |
| T_{stg} | storage temperature | | -65 | 150 | °C |
| T_j | junction temperature | | - | 150 | °C |



$$T_j \leq T_{j(max)} \text{ } ^\circ\text{C}$$

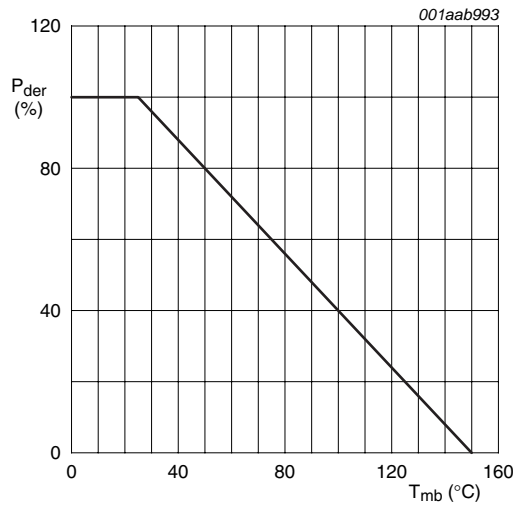
Fig 1. Reverse bias safe operating area



$$V_{CL(CE)} \leq 1000 \text{ V}; V_{CC} = 150 \text{ V}; V_{BB} = -5 \text{ V};$$

$$L_B = 1 \mu\text{H}; L_C = 200 \mu\text{H}$$

Fig 2. Test circuit for reverse bias safe operating area



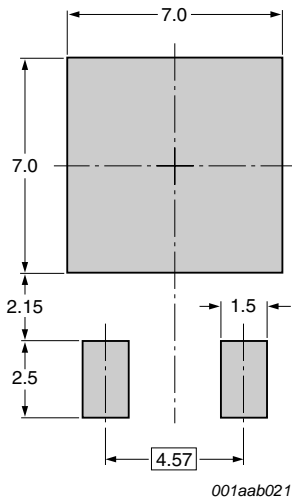
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100 \%$$

Fig 3. Normalized total power dissipation as a function of mounting base temperature

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|--|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 5 | - | - | 1.56 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | printed-circuit-board mounted; minimum footprint; see Figure 4 | - | 75 | - | K/W |



all dimensions are in mm

Fig 4. Minimum footprint SOT428

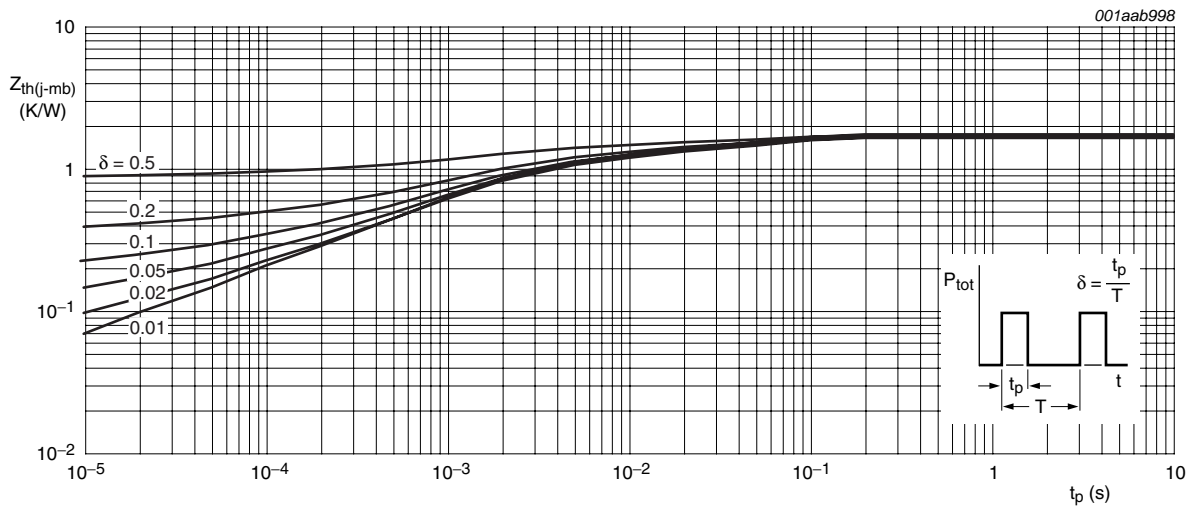


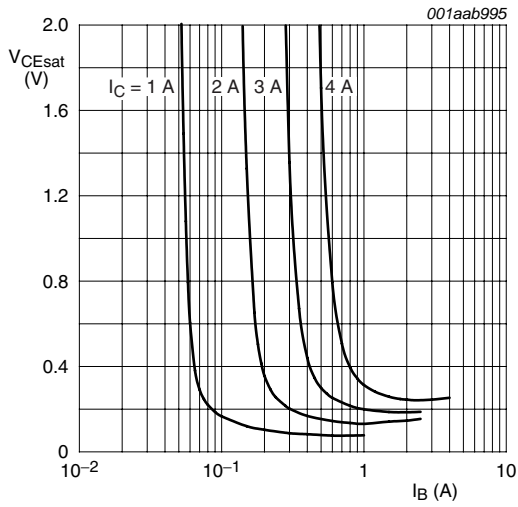
Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

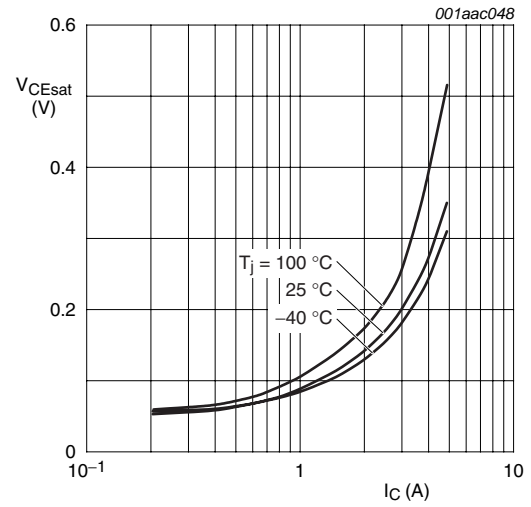
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit | |
|--------------------------------|--------------------------------------|--|-----|-------|------|---------------|----|
| Static characteristics | | | | | | | |
| I_{CES} | collector-emitter cut-off current | $V_{BE} = 0\text{ V}; V_{CE} = 700\text{ V}; T_j = 25\text{ }^\circ\text{C}$ | [1] | - | - | 0.2 | mA |
| | | $V_{BE} = 0\text{ V}; V_{CE} = 700\text{ V}; T_j = 125\text{ }^\circ\text{C}$ | [1] | - | - | 0.5 | mA |
| I_{CBO} | collector-base cut-off current | $V_{CB} = 700\text{ V}; I_E = 0\text{ A}$ | [1] | - | - | 0.2 | mA |
| I_{CEO} | collector-emitter cut-off current | $V_{CE} = 400\text{ V}; I_B = 0\text{ A}$ | [1] | - | - | 0.1 | mA |
| I_{EBO} | emitter-base cut-off current | $V_{EB} = 9\text{ V}; I_C = 0\text{ A}$ | - | - | 10 | mA | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 4\text{ A}; I_B = 0.8\text{ A}$; see Figure 6 ; see Figure 7 | - | 0.35 | 1 | V | |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 4\text{ A}; I_B = 0.8\text{ A}$; see Figure 8 | - | 1 | 1.5 | V | |
| V_F | forward voltage | $I_F = 4\text{ A}; T_j = 25\text{ }^\circ\text{C}$ | - | 1.07 | 1.5 | V | |
| h_{FE} | DC current gain | $I_C = 4\text{ A}; V_{CE} = 5\text{ V}; T_{mb} = 25\text{ }^\circ\text{C}$; see Figure 9 ; see Figure 10 | 8 | 12.5 | - | | |
| | | $I_C = 1\text{ mA}; V_{CE} = 5\text{ V}; T_{mb} = 25\text{ }^\circ\text{C}$ | 10 | 17 | 34 | | |
| | | $I_C = 500\text{ mA}; V_{CE} = 5\text{ V}; T_{mb} = 25\text{ }^\circ\text{C}$ | 13 | 22 | 36 | | |
| Dynamic characteristics | | | | | | | |
| t_{on} | turn-on time | $I_C = 5\text{ A}; I_{Bon} = 1\text{ A}; I_{Boff} = -1\text{ A}$; $R_L = 75\text{ }\Omega; T_j = 25\text{ }^\circ\text{C}$; resistive load; see Figure 11 ; see Figure 12 | - | 0.65 | 1 | μs | |
| t_s | storage time | $I_C = 5\text{ A}; I_{Bon} = 1\text{ A}; V_{BB} = -5\text{ V}$; $L_B = 1\text{ }\mu\text{H}; T_j = 25\text{ }^\circ\text{C}$; inductive load; see Figure 13 ; see Figure 14 | - | 1.8 | 2.5 | μs | |
| | | $I_C = 5\text{ A}; I_{Bon} = 1\text{ A}; V_{BB} = -5\text{ V}$; $L_B = 1\text{ }\mu\text{H}; T_j = 25\text{ }^\circ\text{C}$; inductive load; see Figure 13 ; see Figure 14 | - | 1.2 | 1.7 | μs | |
| | | $I_C = 5\text{ A}; I_{Bon} = 1\text{ A}; V_{BB} = -5\text{ V}$; $L_B = 1\text{ }\mu\text{H}; T_j = 100\text{ }^\circ\text{C}$; inductive load; see Figure 13 ; see Figure 14 | - | 1.4 | 1.9 | μs | |
| t_f | fall time | $I_C = 5\text{ A}; I_{Bon} = 1\text{ A}; V_{BB} = -5\text{ V}$; $L_B = 1\text{ }\mu\text{H}; T_{mb} = 25\text{ }^\circ\text{C}$; inductive load; see Figure 13 ; see Figure 14 | - | 0.02 | 0.05 | μs | |
| | | $I_C = 5\text{ A}; I_{Bon} = 1\text{ A}; V_{BB} = -5\text{ V}$; $L_B = 1\text{ }\mu\text{H}; T_{mb} = 100\text{ }^\circ\text{C}$; inductive load; see Figure 13 ; see Figure 14 | - | 0.025 | 0.1 | μs | |
| | | $I_C = 5\text{ A}; I_{Bon} = 1\text{ A}; I_{Boff} = -1\text{ A}$; $R_L = 75\text{ }\Omega; T_j = 25\text{ }^\circ\text{C}$; resistive load; see Figure 11 ; see Figure 12 | - | 0.3 | 0.5 | μs | |

[1] Measured with half-sine wave voltage (curve tracer).



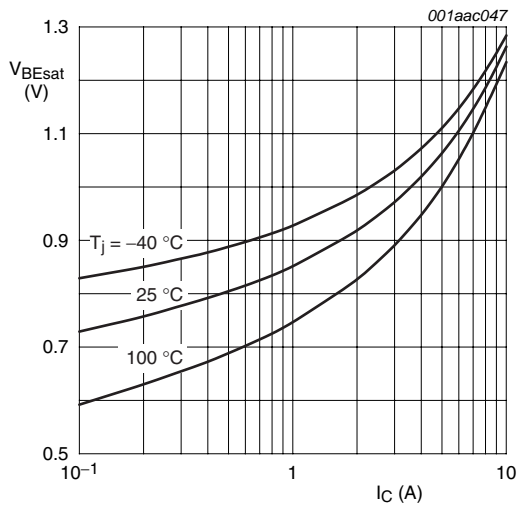
$T_j = 25\text{ }^\circ\text{C}$

Fig 6. Collector-emitter saturation voltage as a function of base current; typical values



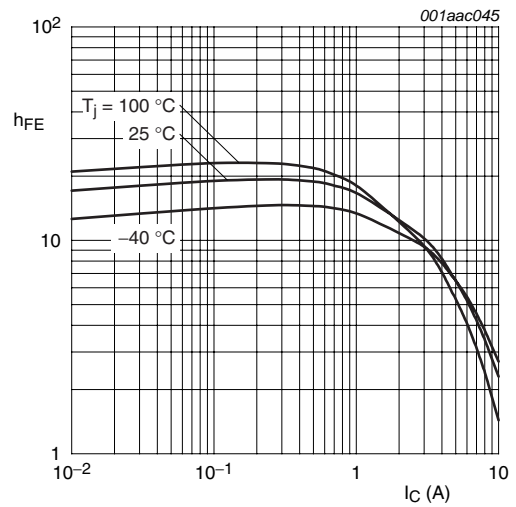
$I_C / I_B = 4$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C / I_B = 4$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = 1\text{ V}$

Fig 9. DC current gain as a function of collector current; typical values

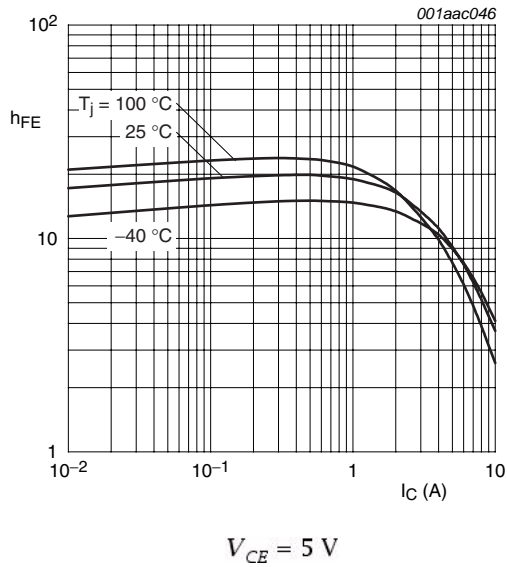
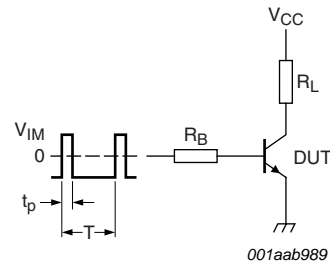


Fig 10. DC current gain as a function of collector current; typical values



$V_{IM} = -6\text{ to }+8\text{ V}; V_{CC} = 250\text{ V}; t_p = 20\ \mu\text{s}; \delta = \frac{t_p}{T} = 0.01$
 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 11. Test circuit for resistive load switching

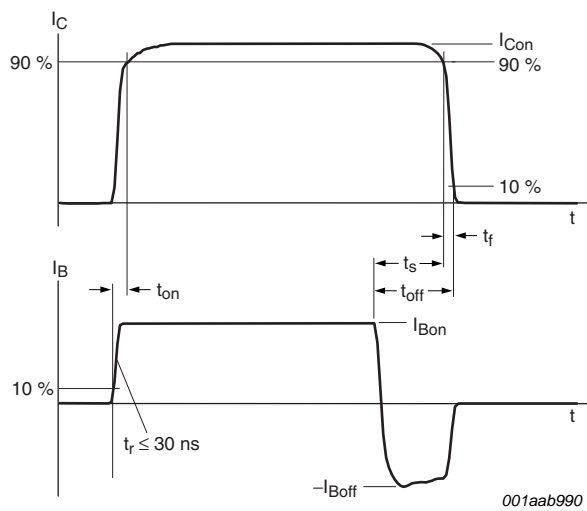
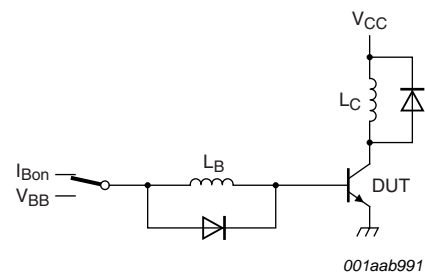


Fig 12. Switching times waveforms for resistive load



$V_{CC} = 300\text{ V}; V_{BB} = -5\text{ V}; L_C = 200\ \mu\text{H}; L_B = 1\ \mu\text{H}$

Fig 13. Test circuit for inductive load switching

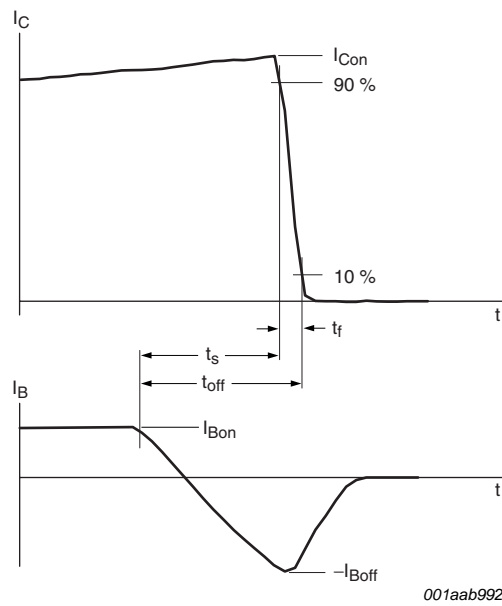


Fig 14. Switching times waveforms for inductive load

7. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

SOT428

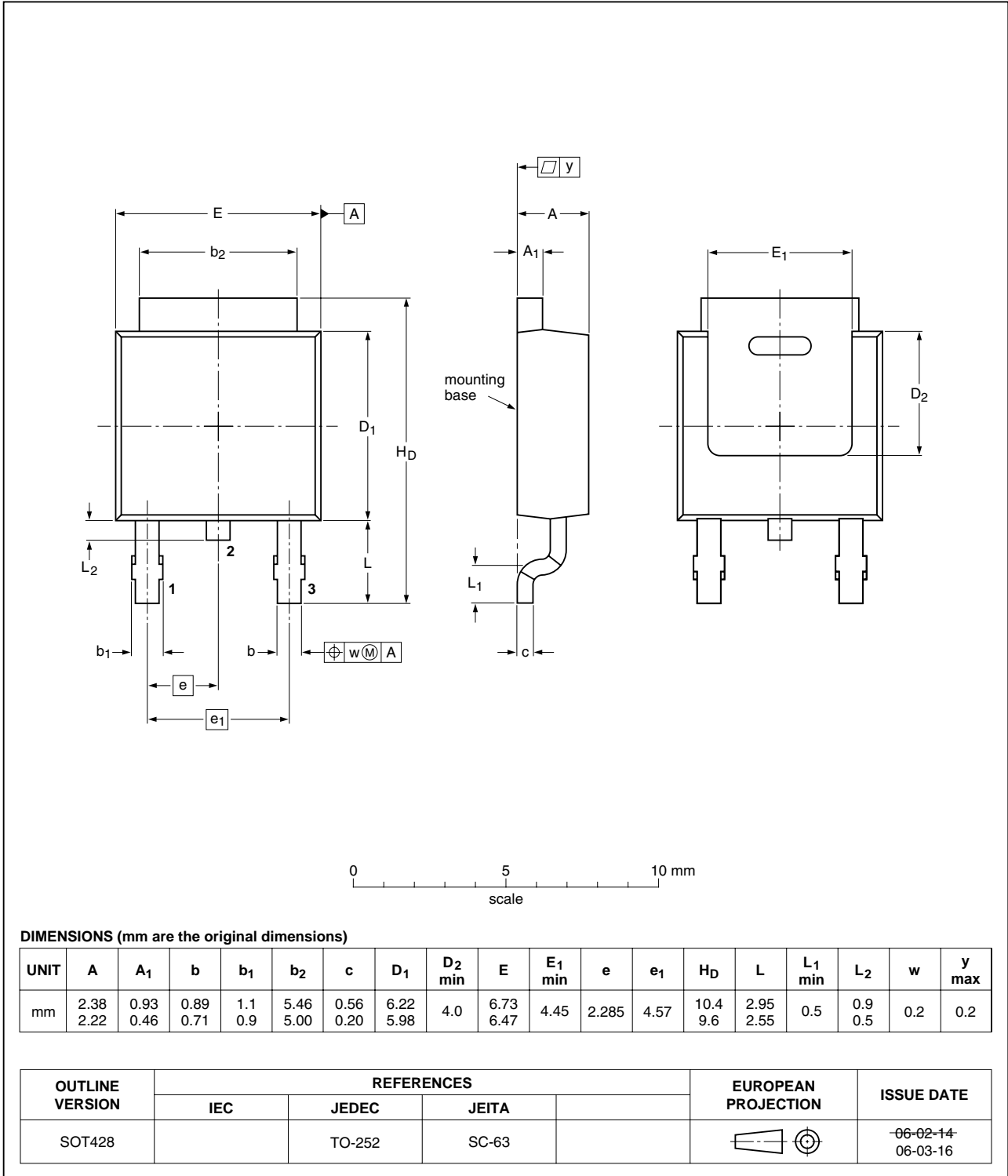


Fig 15. Package outline SOT428 (DPAK)

8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|-------------------------------|--------------------|---------------|---------------|
| BUJD105AD v.2 | 20100729 | Product data sheet | - | BUJD105AD v.1 |
| Modifications: | • Various changes to content. | | | |
| BUJD105AD v.1 | 20090508 | Product data sheet | - | - |

9. Legal information

9.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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[2] The term 'short data sheet' is explained in section "Definitions".

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